



<b>Session Title:</b>	<b>[MB2] Power Device II</b>
<b>Session Date:</b>	<b>November 20 (Mon.), 2023</b>
<b>Session Time:</b>	<b>14:55-16:35</b>
<b>Session Room:</b>	<b>Room B (Grand Ballroom 1, 2F)</b>
<b>Session Chair:</b>	<b>Prof. Hojun Lee (Pusan Nat'l Univ., Korea)</b>

**[MB2-1] [Invited] 14:55-15:15**

**GaN Power Devices for High Temperature and High Voltage Applications**

Hyung-Seok Lee, Donghan Kim, Sooyoung Moon, Dong-Young Kim, Zin-Sig Kim, Eun-Soo Nam, and Sung-Bum Bae (ETRI, Korea)

**[MB2-2] 15:15-15:35**

**A Study on 4H-SiC Single Crystal Growth Using Recycled Powders**

Im Gyu Yeo, Jae Yoon Lee, Han Seok Seo, Myoung Chul Chun, and Tai Hee Eun (RIST, Korea)

**[MB2-3] 15:35-15:55**

**3D-Printed Micro-Intersection of Thin/Thick Films for Ultrafast Charge Transport**

Myeong-Hun Jo and Hyo-Jin Ahn (Seoul Nat'l Univ. Science and Tech., Korea)

**[MB2-4] 15:55-16:15**

**Design Optimization of 1.2 kV SiC Trench MOSFETs**

Yeongeun Park, Hyowon Yoon, Chaeyun Kim, Sangyeob Kim, Gyuhyeok Kang, Gukhwa Jeon, Jinhun Kim, Sumin Park, Kanghee Shin, Dusan Baek (Kumoh Nat'l Inst. of Tech., Korea), Jaejin Song, Jeongyun Lee, Soontak Kwon (KEC, Korea), and Ogyun Seok (Kumoh Nat'l Inst. of Tech., Korea)

**[MB2-5] 16:15-16:35**

**Enhancement of Low Specific On-Resistance and Reduced Switching Loss in 4H-SiC Single-Channel MOSFET with Extend P-Layer**

Jee-hun Jeong, Min-Seok Jang, Dahui Yoo, Jung-Bok Lee, and Ho-Jun Lee (Pusan Nat'l Univ., Korea)